



LIS3L02AQ5

MEMS INERTIAL SENSOR: 3-axis - $\pm 2g/\pm 6g$ LINEAR ACCELEROMETER

PRELIMINARY DATA

Features

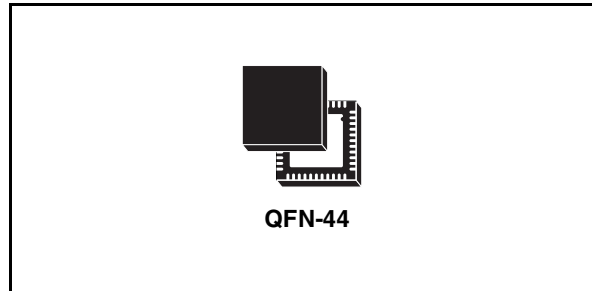
- 4.5V TO 5.5V SINGLE SUPPLY OPERATION
- LOW POWER CONSUMPTION
- $\pm 2g/\pm 6g$ USER SELECTABLE FULL-SCALE
- 0.5mg RESOLUTION OVER 100Hz BANDWIDTH
- EMBEDDED SELF TEST AND POWER DOWN
- OUTPUT VOLTAGE, OFFSET AND SENSITIVITY RATIO METRIC TO THE SUPPLY VOLTAGE
- HIGH SHOCK SURVIVABILITY
- ECO-PACK COMPLIANT

Description

The LIS3L02AQ5 is a low-power 3-axis linear capacitive accelerometer that includes a sensing element and an IC interface able to take the information from the sensing element and to provide an analog signal to the external world.

The sensing element, capable of detecting the acceleration, is manufactured using a dedicated process developed by ST to produce inertial sensors and actuators in silicon.

The IC interface is manufactured using a standard CMOS process that allows high level of integration



to design a dedicated circuit which is trimmed to better match the sensing element characteristics.

The LIS3L02AQ5 has a user selectable full scale of $\pm 2g$, $\pm 6g$ and it is capable of measuring accelerations over a bandwidth of 1.5 KHz for all axes. The device bandwidth may be reduced by using external capacitances. A self-test capability allows to check the mechanical and electrical signal path of the sensor.

The LIS3L02AQ5 is available in plastic SMD package and it is specified over an extended temperature range of -40°C to $+85^{\circ}\text{C}$.

The LIS3L02AQ5 belongs to a family of products suitable for a variety of applications:

- Mobile terminals
- Gaming and Virtual Reality input devices
- Free-fall detection for data protection
- Antitheft systems and Inertial Navigation
- Appliance and Robotics.

Order codes

| Part number | Temp range, $^{\circ}\text{C}$ | Package | Packing |
|--------------|--|---------|-------------|
| LIS3L02AQ5 | -40°C to $+85^{\circ}\text{C}$ | QFN-44 | Tray |
| LIS3L02AQ5TR | -40°C to $+85^{\circ}\text{C}$ | QFN-44 | Tape & Reel |

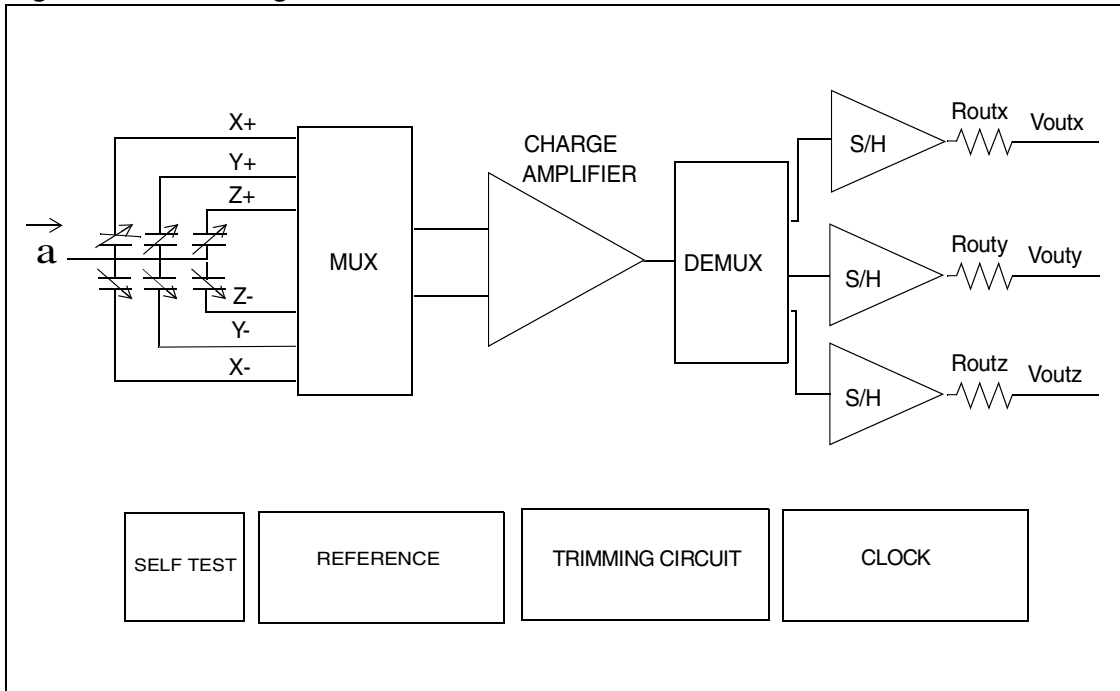
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1 Block Diagram & Pins Description

1.1 Block diagram

Figure 1. Block Diagram



1.2 Pins Description

Figure 2. Pins Connection (Top view)

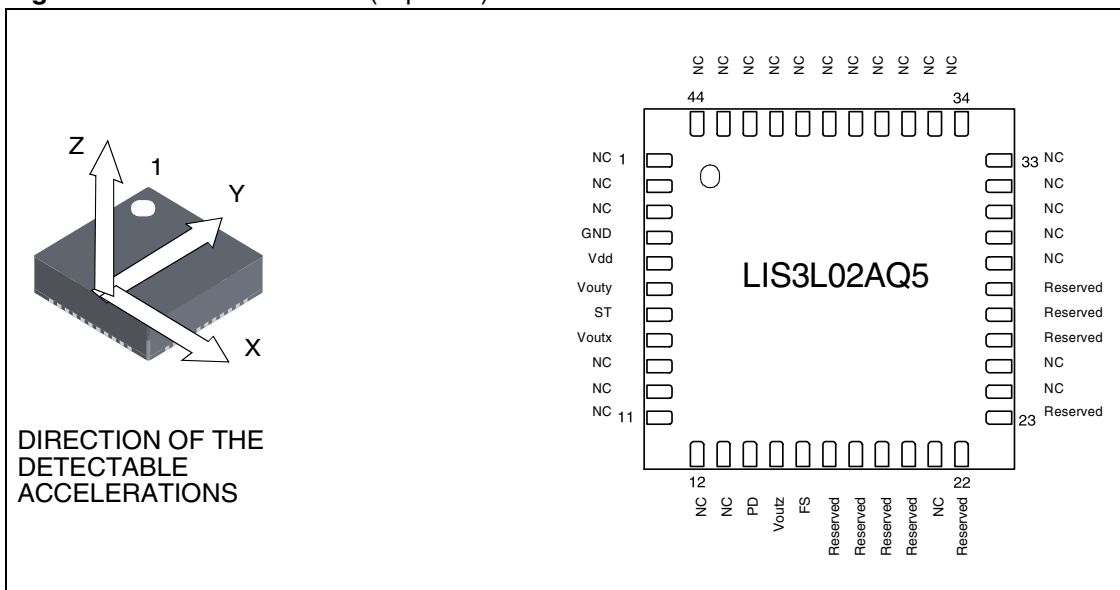


Table 1. Pins description

| Pin # | Pin Name | Function |
|--------|----------|---|
| 1 to 3 | NC | Internally not connected |
| 4 | GND | 0V supply |
| 5 | Vdd | Power supply |
| 6 | Vouty | Output Voltage, y-channel |
| 7 | ST | Self Test (Logic 0: normal mode; Logic 1: Self-test) |
| 8 | Voutx | Output Voltage, x-channel |
| 9-13 | NC | Internally not connected |
| 14 | PD | Power Down (Logic 0: normal mode; Logic 1: Power-Down mode) |
| 15 | Voutz | Output Voltage, z-channel |
| 16 | FS | Full Scale selection (Logic 0: $\pm 2g$ Full-scale; Logic 1: $\pm 6g$ Full-scale) |
| 17-18 | Reserved | Leave unconnected |
| 19 | Reserved | Leave unconnected |
| 20 | Reserved | Leave unconnected |
| 21 | NC | Internally not connected |
| 22-23 | Reserved | Leave unconnected |
| 24-25 | NC | Internally not connected |
| 26 | Reserved | Connect to Vdd or GND |
| 27 | Reserved | Leave unconnected or connect to Vdd |
| 28 | Reserved | Leave unconnected or connect to GND |
| 29-44 | NC | Internally not connected |

2 Mechanical and Electrical Specifications

2.1 Mechanical Characteristics.

Table 2. Mechanical Characteristics¹

(Temperature range -40°C to +85°C) All the parameters are specified @ Vdd =5.0V,
T = 25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Typ. ² | Max. | Unit |
|---------|--|--|------------|-------------------|------------|--|
| Ar | Acceleration Range ³ | FS pin connected to GND | ±1.8 | ±2.0 | | g |
| | | FS pin connected to Vdd | ±5.4 | ±6.0 | | g |
| So | Sensitivity ⁴ | Full-scale = 2g | Vdd/5-10% | Vdd/5 | Vdd/5+10% | V/g |
| | | Full-scale = 6g | Vdd/15-10% | Vdd/15 | Vdd/15+10% | V/g |
| SoDr | Sensitivity Change Vs Temperature | Delta from +25°C | | ±0.01 | | %/°C |
| Voff | Zero-g Level ⁴ | T = 25°C | Vdd/2-6% | Vdd/2 | Vdd/2+6% | V |
| OffDr | Zero-g Level Change Vs Temperature | Delta from +25°C | | ±0.8 | | mg/°C |
| NL | Non Linearity ⁵ | Best fit straight line Full-scale = 2g X, Y axis | | ±0.3 | ±1.5 | % FS |
| | | Best fit straight line Full-scale = 2g Z axis | | ±0.6 | ±2 | % FS |
| CrossAx | Cross-Axis ⁶ | | | ±2 | ±4 | % |
| An | Acceleration Noise Density | Vdd=5.0V; Full-scale = 2g | | 50 | | $\frac{\mu\text{g}}{\sqrt{\text{Hz}}}$ |
| Vt | Self Test Output Voltage Change ^{7,8,9} | T = 25°C Vdd=5.0V Full-scale = 2g X axis | -70 | -140 | -320 | mV |
| | | T = 25°C Vdd=5.0V Full-scale = 2g Y axis | 70 | 140 | 320 | mV |
| | | T = 25°C Vdd=5.0V Full-scale = 2g Z axis | 70 | 140 | 320 | mV |

Table 2. Mechanical Characteristics¹ (continued)
 (Temperature range -40°C to +85°C) All the parameters are specified @ Vdd =5.0V,
 T = 25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Typ. ² | Max. | Unit |
|--------|---|----------------|------|-------------------|------|------|
| Fres | Sensing Element Resonance Frequency ¹⁰ | all axes | 1.5 | | | KHz |
| Top | Operating Temperature Range | | -40 | | +85 | °C |
| Wh | Product Weight | | | 0.2 | | gram |

Note: 1 The product is factory calibrated at 5.0V. The device can be powered from 4.5V to 5.5V. Voff, So and Vt parameters will vary with supply voltage.

- 2 Typical specifications are not guaranteed
- 3 Guaranteed by wafer level test and measurement of initial offset and sensitivity
- 4 Zero-g level and sensitivity are essentially ratiometric to supply voltage
- 5 Guaranteed by design
- 6 Contribution to the measuring output of the inclination/acceleration along any perpendicular axis
- 7 Self test "output voltage change" is defined as $V_{out}(V_{st=Logic1}) - V_{out}(V_{st=Logic0})$
- 8 Self test "output voltage change" varies cubically with supply voltage
- 9 When full-scale is set to ±6g, self-test "output voltage change" is one third of the specified value
- 10 Minimum resonance frequency $F_{res}=1.5\text{KHz}$. Sensor bandwidth= $1/(2*\pi*110\text{K}\Omega*C_{load})$ with $C_{load}>1\text{nF}$.

2.2 Electrical Characteristics

Table 3. Electrical Characteristics¹

(Temperature range -40°C to +85°C) All the parameters are specified @ Vdd =5.0V, T=25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Typ. ² | Max. | Unit |
|--------|---|---------------------------------------|------|-------------------|------|------|
| Vdd | Supply Voltage | | 4.5 | 5.0 | 5.5 | V |
| Idd | Supply Current | mean value PD pin connected to GND | | 1.0 | 1.5 | mA |
| IddPdn | Supply Current in Power Down Mode | rms value PD pin connected to Vdd | | 2.5 | 5 | μA |
| Vst | Self Test Input | Logic 0 level | 0 | | 0.8 | V |
| | | Logic 1 level | 2.2 | | Vdd | V |
| Rout | Output Impedance | | 80 | 110 | 140 | kΩ |
| Cload | Capacitive Load Drive ³ | | 320 | | | pF |
| Ton | Turn-On Time at Exit From Power Down Mode | Load in μF | | 550*Cload+0.3 | | ms |
| Top | Operating Temperature Range | | -40 | | +85 | °C |

Note: 1 The product is factory calibrated at 5.0V

2 Typical specifications are not guaranteed

3 Minimum resonance frequency $F_{res}=1.5\text{KHz}$. Sensor bandwidth= $1/(2*\pi*110\text{K}\Omega*Cload)$ with $Cload>1\text{nF}$

2.3 Absolute maximum ratings

Stresses above those listed as “absolute maximum ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 4. Absolute maximum ratings

| Symbol | Ratings | Maximum Value | Unit |
|------------------|---|-------------------|------|
| Vdd | Supply voltage | -0.3 to 7 | V |
| Vin | Input Voltage on Any Control pin (FS, PD, ST) | -0.3 to Vdd +0.3 | V |
| A _{POW} | Acceleration (Any axis, Powered, Vdd=3.3V) | 3000g for 0.5 ms | |
| | | 10000g for 0.1 ms | |
| A _{UNP} | Acceleration (Any axis, Not powered) | 3000g for 0.5 ms | |
| | | 10000g for 0.1 ms | |
| T _{STG} | Storage Temperature Range | -40 to +125 | °C |
| ESD | Electrostatic Discharge Protection | 2KV HBM | |
| | | 200V MM | |
| | | 1500V CDM | |



This is a Mechanical Shock sensitive device, improper handling can cause permanent damages to the part



This is an ESD sensitive device, improper handling can cause permanent damages to the part

2.4 Terminology

Sensitivity describes the gain of the sensor and can be determined by applying 1g acceleration to it. As the sensor can measure DC accelerations this can be done easily by pointing the axis of interest towards the center of the earth, note the output value, rotate the sensor by 180 degrees (point to the sky) and note the output value again thus applying $\pm 1g$ acceleration to the sensor. Subtracting the larger output value from the smaller one and dividing the result by 2 will give the actual sensitivity of the sensor. This value changes very little over temperature (see sensitivity change vs. temperature) and also very little over time. The Sensitivity Tolerance describes the range of Sensitivities of a large population of sensors.

Zero-g level describes the actual output signal if there is no acceleration present. A sensor in a steady state on a horizontal surface will measure 0g in X axis and 0g in Y axis whereas the Z axis will measure +1g. The output is ideally for a 5.0V powered sensor $V_{dd}/2 = 2500mV$. A deviation from ideal 0-g level (2500mV in this case) is called Zero-g offset. Offset of precise MEMS sensors is to some extent a result of stress to the sensor and therefore the offset can slightly change after mounting the sensor onto a printed circuit board or exposing it to extensive mechanical stress. Offset changes little over temperature - see "Zero-g level change vs. temperature" - the Zero-g level of an individual sensor is very stable over lifetime. The Zero-g level tolerance describes the range of zero-g levels of a population of sensors.

Self Test allows to test the mechanical and electrical part of the sensor. By applying a digital signal to the ST input pin an internal reference is switched to a certain area of the sensor and creates a defined deflection of the moveable structure. The sensor will generate a defined signal and the interface chip will perform the signal conditioning. If the output signal changes with the specified amplitude than the sensor is working properly and the parameters of the interface chip are within the defined specifications.

Output impedance describes the resistor inside the output stage of each channel. This resistor is part of a filter consisting of an external capacitor of at least 320pF and the internal resistor. Due to the high resistor level only small, inexpensive external capacitors are needed to generate low corner frequencies. When interfacing with an ADC it is important to use high input impedance input circuitries to avoid measurement errors. Note that the minimum load capacitance forms a corner frequency beyond the resonance frequency of the sensor. For a flat frequency response a corner frequency well below the resonance frequency is recommended. In general the smallest possible bandwidth for an particular application should be chosen to get the best results.

3 Functionality

The LIS3L02AQ5 is a high performance, low-power, analog output 3-axis linear accelerometer packaged in a QFN package. The complete device includes a sensing element and an IC interface able to take the information from the sensing element and to provide an analog signal to the external world.

3.1 Sensing element

A proprietary process is used to create a surface micro-machined accelerometer. The technology allows to carry out suspended silicon structures which are attached to the substrate in a few points called anchors and are free to move in the direction of the sensed acceleration. To be compatible with the traditional packaging techniques a cap is placed on top of the sensing element to avoid blocking the moving parts during the moulding phase of the plastic encapsulation.

When an acceleration is applied to the sensor the proof mass displaces from its nominal position, causing an imbalance in the capacitive half-bridge. This imbalance is measured using charge integration in response to a voltage pulse applied to the sense capacitor.

At steady state the nominal value of the capacitors are few pF and when an acceleration is applied the maximum variation of the capacitive load is up to 100fF.

3.2 IC Interface

In order to increase robustness and immunity against external disturbances the complete signal processing chain uses a fully differential structure. The final stage converts the differential signal into a single-ended one to be compatible with the external world.

The signals of the sensing element are multiplexed and fed into a low-noise capacitive charge amplifier that implements a Correlated Double Sampling system (CDS) at its output to cancel the offset and the 1/f noise. The output signal is de-multiplexed and transferred to three different S&Hs, one for each channel and made available to the outside.

The low noise input amplifier operates at 200 kHz while the three S&Hs operate at a sampling frequency of 66 kHz. This allows a large oversampling ratio, which leads to in-band noise reduction and to an accurate output waveform.

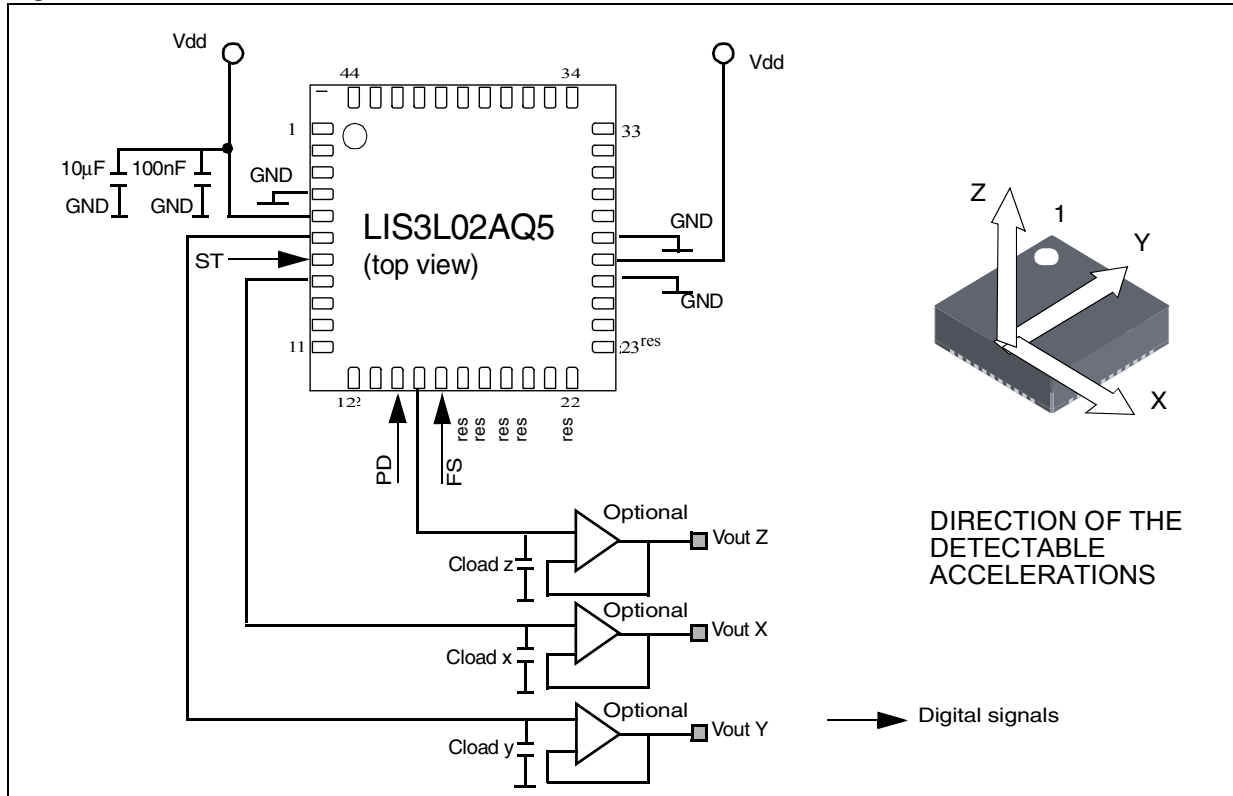
All the analog parameters (zero-g level, sensitivity and self-test) are ratiometric to the supply voltage. Increasing or decreasing the supply voltage, the sensitivity and the offset will increase or decrease almost linearly. The self test voltage change varies cubically with the supply voltage.

3.3 Factory calibration

The IC interface is factory calibrated for sensitivity (S_0) and Zero-g level (V_{off}). The trimming values are stored inside the device by a non volatile structure. Any time the device is turned on, the trimming parameters are downloaded into the registers to be employed during the normal operation. This allows the user to employ the device without further calibration.

4 Application hints

Figure 3. LIS3L02AQ5 Electrical Connection



Power supply decoupling capacitors (100nF ceramic or polyester + 10µF Aluminum) should be placed as near as possible to the device (common design practice).

The LIS3L02AQ5 allows to band limit Voutx, Vouty and Voutz through the use of external capacitors. The re-com-mended frequency range spans from DC up to 1.5 KHz. In particular, capacitors must be added at output pins to implement low-pass filtering for antialiasing and noise reduction. The equation for the cut-off frequency (f_t) of the external filters is:

$$f_t = \frac{1}{2\pi \cdot R_{out} \cdot C_{load}(x, y, z)}$$

Taking into account that the internal filtering resistor (R_{out}) has a nominal value equal to 110kOhm, the equation for the external filter cut-off frequency may be simplified as follows:

$$f_t = \frac{1.45\mu F}{C_{load}(x, y, z)}$$

The tolerance of the internal resistor can vary typically of $\pm 20\%$ within its nominal value of 110kΩ; thus the cut-off frequency will vary accordingly. A minimum capacitance of 320 pF for $C_f(x, y, z)$ is required in any case.

Table 5. Filter Capacitor Selection, C_f (x,y,z). Commercial capacitance value choose.

| Cut-off frequency | Capacitor value |
|-------------------|-----------------|
| 1 Hz | 1500 nF |
| 10 Hz | 150 nF |
| 20 Hz | 68 nF |
| 50 Hz | 30 nF |
| 100 Hz | 15 nF |
| 200 Hz | 6.8 nF |
| 500 Hz | 3 nF |

4.1 Soldering information

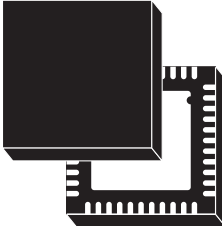
The QFN44 package is lead free and green package qualified for soldering heat resistance according to JEDEC J-STD-020C. Land pattern and soldering recommendations are available upon request.

5 Package Information

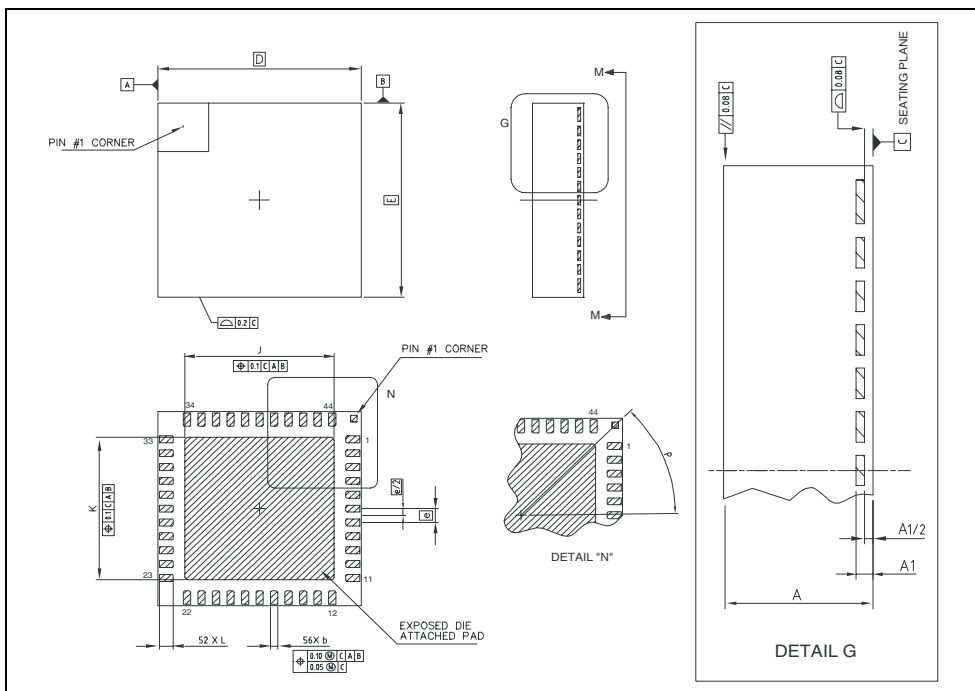
Figure 4. QFN-44 Mechanical Data & Package Dimensions

| DIM. | mm | | | inch | | |
|------|------|--------|------|-------|--------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 1.70 | 1.80 | 1.90 | 0.067 | 0.071 | 0.075 |
| A1 | 0.19 | | 0.21 | 0.007 | | 0.008 |
| b | 0.20 | 0.25 | 0.30 | 0.008 | 0.01 | 0.012 |
| D | | 7.0 | | | 0.276 | |
| E | | 7.0 | | | 0.276 | |
| e | | 0.50 | | | 0.020 | |
| J | 5.04 | | 5.24 | 0.198 | | 0.206 |
| K | 5.04 | | 5.24 | 0.198 | | 0.206 |
| L | 0.38 | 0.48 | 0.58 | 0.015 | 0.019 | 0.023 |
| P | | 45 REF | | | 45 REF | |

OUTLINE AND MECHANICAL DATA



**QFN-44 (7x7x1.8mm)
Quad Flat Package No lead**



6 Revision history

| Date | Revision | Changes |
|--------------|----------|--------------|
| 14-July-2005 | 1 | First issue. |

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